

CLAIM

What is claimed is:

1. An improved processing method for the packaging technique of a large size FED comprising the steps of:
 - 5 providing an ITO conducting glass;
forming a BM layer area, a multi-phosphor layer area and a hollow area on an ITO conducting glass using the first screen mask and the second screen mask, and forming a Cr/CrO_x layer area in the hollow area;
 - 10 forming an Al layer on said areas, then carrying out a sintering process of phosphor layer to form an AlO_x layer;
fixing a spacer on the hollow area of the AlO_x layer; and
aligning process for a lower plate.
2. An improved packaging technique of a large size FED of claim 1, wherein the method of forming an Al layer is an evaporation, the
15 thickness is about 1000-3000 angstroms.
3. An improved packaging technique of a large size FED of claim 1, wherein the temperatures of the sintering process of the phosphor layer is about 500-560 °C.
- 20 4. An improved packaging technique of a large size FED of claim 1, wherein the thickness of the AlO_x layer is around 50-200 angstroms.
5. An improved packaging technique of a large size FED of claim 1, wherein the thickness of the Cr/CrO_x layer is around 1000-3000
25 angstroms.

6. An improved packaging technique of a large size FED of claim 1, wherein the spacer is form as a column structure, and the height of the spacer is about 1.1 mm.
7. An improved packaging technique of a large size FED of claim 1, wherein there is a plurality of bonding areas between the spacer and the AlO_x layer.
8. An improved packaging technique of a large size FED of claim 1, wherein said method of fixing the spacer is an anodic bonding technique.
9. An improved packaging technique of a large size FED of claim 1, wherein the voltage of fixing the spacer is 1.00-1.50 V/ μm .
10. An improved packaging technique of a large size FED of claim 1, wherein the temperature of fixing the substrate glass of the spacer is 200-300 $^{\circ}\text{C}$.
11. An improved structure for the packaging technique of a large size FED comprising of:
 - an ITO conducting glass;
 - on the ITO conducting glass is defined to a BM layer area, a multi-phosphor layer area, and a hollow area, in which the inside of
 - a hollow area is formed a Cr/CrO_x layer area;
 - said areas are coated with an Al layer;
 - an Al layer is coated with an AlO_x layer;
 - a spacer is fixed on an AlO_x layer of the hollow area; and
 - a lower plate is fixed on the spacer.
12. An improved packaging technique of a large size FED of

- claim11, wherein said method of forming an Al layer is an evaporation, and the thickness is around 1000-3000 angstroms.
13. An improved packaging technique of a large size FED of claim11, wherein the temperature of the sintering process of the phosphor layer is around 500-560 °C.
14. An improved packaging technique of a large size FED of claim 11, wherein the thickness of the AlO_x layer is around 50-200 angstroms.
15. An improved packaging technique of a large size FED of claim 11, wherein said the thickness of the Cr/CrO_x layer is around 1000-3000 angstroms.
16. An improved packaging technique of a large size FED of claim 11, wherein said spacer is form as a column structure, and the height of the spacer is about 1.1 mm.
17. An improved packaging technique of a large size FED of claim 11, wherein there is a plurality of bonding areas between the spacer and an AlO_x layer.
18. An improved packaging technique of a large size FED of claim 11, wherein said method of fixing the spacer is an anodic bonding technique.
19. An improved packaging technique of a large size FED of claim 11, wherein the voltage of fixing the spacer is 1.00-1.50 V/ μm .
20. An improved packaging technique of a large size FED of claim 11, wherein the temperature of fixing the substrate glass of the spacer is 200-300 °C.